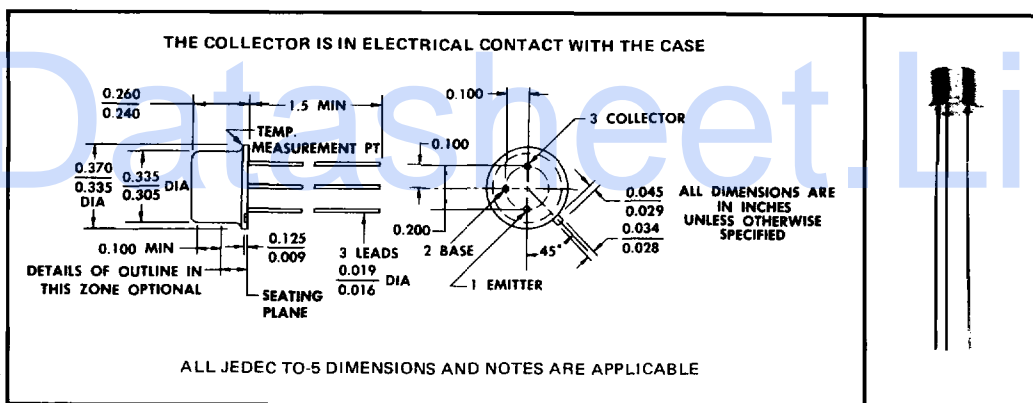


TYPES 2N3719, 2N3720 P-N-P SILICON POWER TRANSISTORS

FOR POWER-AMPLIFIER AND HIGH-SPEED-SWITCHING APPLICATIONS
DESIGNED FOR COMPLEMENTARY USE WITH TIP501, TIP502

- Max t_{off} of 0.4 μs at $I_C = 1 A$
- 3-A Rated Continuous Collector Current
- 6 Watts at 25°C Case Temperature
- Min f_T of 60 MHz at 10 V, 0.5 A

*mechanical data



TYPES 2N3719, 2N3720
BULLETIN NO. DLS-711866, DECEMBER 1971

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absolute maximum ratings at 25°C case temperature (unless otherwise noted)

	2N3719	2N3720
* Collector-Base Voltage	-40 V	-60 V
* Collector-Emitter Voltage (See Note 1)	-40 V	-60 V
* Emitter-Base Voltage	-4 V	-4 V
* Continuous Collector Current	←-3 A→	←-3 A→
* Peak Collector Current (See Note 2)	←-10 A→	←-10 A→
* Continuous Base Current	←-0.5 A→	←-0.5 A→
* Safe Operating Areas at (or below) 25°C Case Temperature	See Figures 3 and 4	
* Continuous Device Dissipation at (or below) 25°C Case Temperature (See Note 3)	←6 W→	←6 W→
* Continuous Device Dissipation at (or below) 25°C Free-Air Temperature (See Note 4)	←1 W→	←1 W→
* Operating Collector Junction Temperature Range	-65°C to 200°C	-65°C to 200°C
* Storage Temperature Range	-65°C to 200°C	-65°C to 200°C
* Lead Temperature 1/16 Inch from Case for 10 Seconds	←300°C→	←300°C→

- NOTES: 1. These values apply when the base-emitter diode is open-circuited.
 2. This value applies for $t_{pw} \leq 0.5$ ms, duty cycle $\leq 10\%$.
 3. Derate linearly to 200°C case temperature at the rate of 34.3 mW/°C or refer to Dissipation Derating Curve, Figure 5.
 4. Derate linearly to 200°C free-air temperature at the rate of 5.71 mW/°C or refer to Dissipation Derating Curve, Figure 6.

*JEDEC registered data. This data sheet contains all applicable registered data in effect at the time of publication.

TYPES 2N3719, 2N3720

P-N-P SILICON POWER TRANSISTORS

*electrical characteristics at 25°C case temperature (unless otherwise noted)

PARAMETER	TEST CONDITIONS	2N3719		2N3720		UNIT	
		MIN	MAX	MIN	MAX		
V _{(BR)CEO} Collector-Emitter Breakdown Voltage	I _C = -20 mA, I _B = 0, See Note 5	-40		-60		V	
I _{CEV} Collector Cutoff Current	V _{CE} = -40 V, V _{BE} = 2 V		-10			μA	
	V _{CE} = -60 V, V _{BE} = 2 V			-10			
	V _{CE} = -40 V, V _{BE} = 2 V, T _C = 150°C		-1			mA	
	V _{CE} = -60 V, V _{BE} = 2 V, T _C = 150°C			-1			
I _{CBO} Collector Cutoff Current	V _{CB} = -40 V, I _E = 0		-10			μA	
	V _{CB} = -60 V, I _E = 0			-10			
I _{EBO} Emitter Cutoff Current	V _{EB} = -4 V, I _C = 0		-1	-1		mA	
h _{FE} Static Forward Current Transfer Ratio	V _{CE} = -1.5 V, I _C = -0.5 A		20		20		
	V _{CE} = -1.5 V, I _C = -1 A	See Notes 5 and 6	25	180	25		180
	V _{CE} = -1.5 V, I _C = -1 A, T _C = -40°C		15		15		
V _{BE} Base-Emitter Voltage	I _B = -100 mA, I _C = -1 A, T _C = -40°C to 100°C	See Notes 5 and 6		-1.5		-1.5	V
	I _B = -300 mA, I _C = -3 A, T _C = -40°C to 100°C			-2.3		-2.3	
V _{CE(sat)} Collector-Emitter Saturation Voltage	I _B = -100 mA, I _C = -1 A, T _C = -40°C to 100°C	See Notes 5 and 6		-0.75		-0.75	V
	I _B = -300 mA, I _C = -3 A, T _C = -40°C to 100°C			-1.5		-1.5	
h _{fe} Small-Signal Common-Emitter Forward Current Transfer Ratio	V _{CE} = -10 V, I _C = -0.5 A, f = 30 MHz		2		2		
C _{obo} Common-Base Open-Circuit Output Capacitance	V _{CB} = -10 V, I _E = 0, f = 100 kHz		120		120	pF	
C _{ibo} Common-Base Open-Circuit Input Capacitance	V _{EB} = -0.5 V, I _C = 0, f = 100 kHz		1000		1000	pF	

NOTES: 5. These parameters must be measured using pulse techniques. t_w = 300 μs, duty cycle ≤ 2%.

6. These parameters are measured with voltage-sensing contacts separate from the current-carrying contacts and located within 0.125 inch from the device body.

*switching characteristics at 25°C case temperature

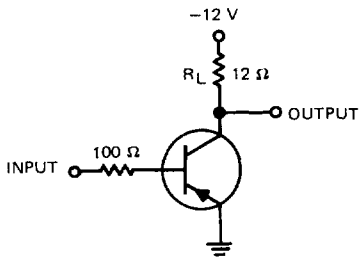
PARAMETER	TEST CONDITIONS†	MAX	UNIT
t _{on} Turn-On Time	I _C = -1 A, I _B (1) = -0.1 A, V _{BE(off)} = 4 V, R _L = 12 Ω, See Figure 1	0.1	μs
t _{off} Turn-Off Time	I _C = -1 A, I _B (1) = -0.1 A, I _B (2) = 0.1 A, R _L = 12 Ω, See Figure 2	0.4	

† Voltage and current values shown are nominal exact values vary slightly with transistor parameters.

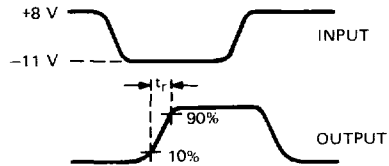
*JEDEC registered data

TYPES 2N3719, 2N3720 P-N-P SILICON POWER TRANSISTORS

*PARAMETER MEASUREMENT INFORMATION



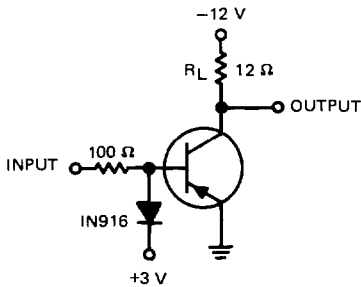
TEST CIRCUIT



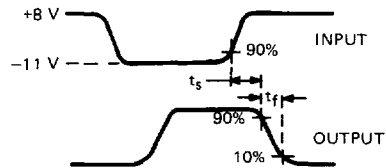
VOLTAGE WAVEFORMS

FIGURE 1—TURN-ON TIME

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TEST CIRCUIT



VOLTAGE WAVEFORMS

FIGURE 2—TURN-OFF TIME

- NOTES:
- The input waveforms are supplied by a generator with the following characteristics: $t_r \leq 10$ ns, $t_f \leq 10$ ns, $Z_{out} = 50$ Ω , $t_w = 10$ μ s, duty cycle $\leq 2\%$.
 - Waveforms are monitored on an oscilloscope with the following characteristics: $t_r \leq 5$ ns, $R_{in} \geq 10$ k Ω , $C_{in} \leq 11.5$ pF.
 - Resistors must be noninductive types.
 - The d-c power supplies may require additional bypassing in order to minimize ringing.

* JEDEC registered data

TYPES 2N3719, 2N3720

P-N-P SILICON POWER TRANSISTORS

MAXIMUM SAFE OPERATING AREAS

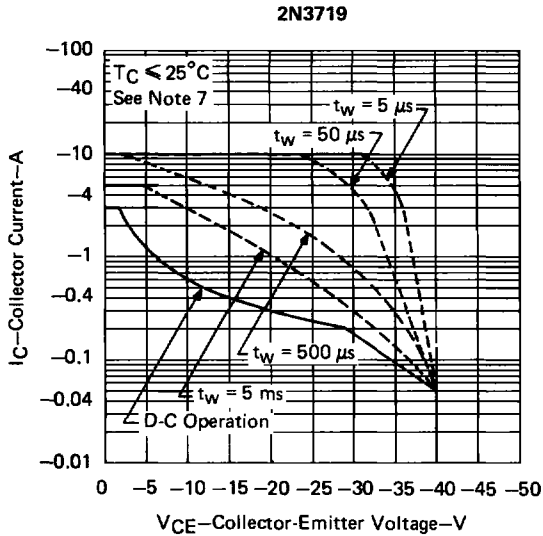


FIGURE 3

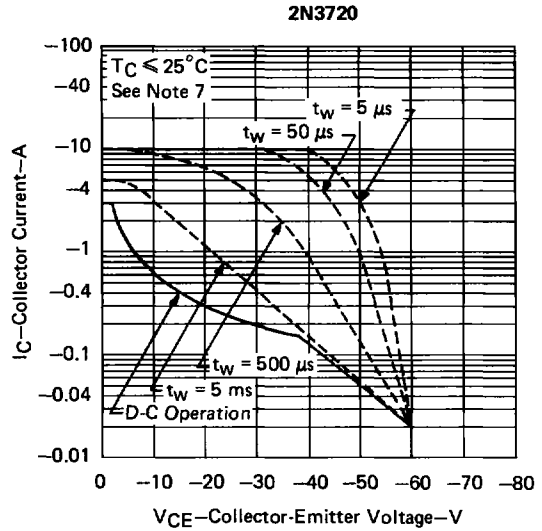


FIGURE 4

NOTE 7: Areas defined by dashed lines apply for nonrepetitive-pulse operation. The pulse may be repeated after the device has regained thermal equilibrium.

THERMAL INFORMATION

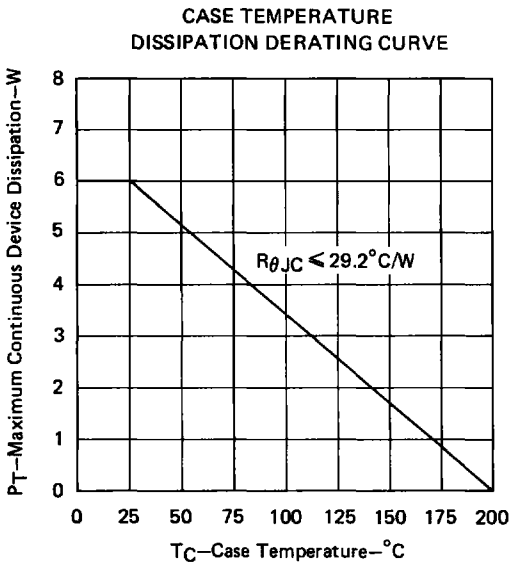


FIGURE 5

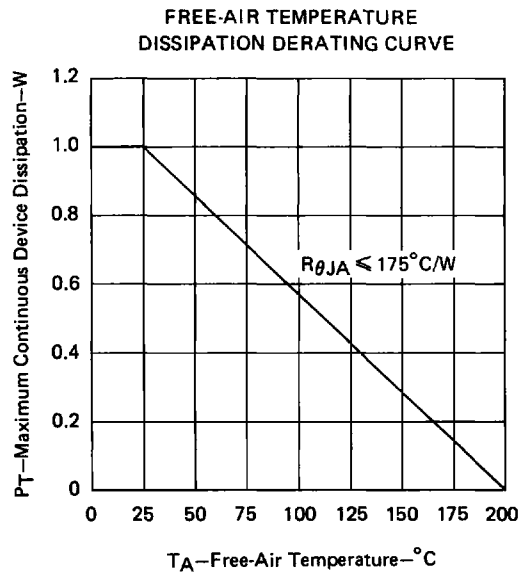


FIGURE 6